

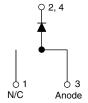
RoHS

HALOGEN

FREE

HEXFRED®, Ultrafast Soft Recovery Diode, 4 A





TO-252AA (D-PAK)

PRODUCT SUMMARY				
Package	TO-252AA (D-PAK)			
I _{F(AV)}	4 A			
V_{R}	600 V			
V _F at I _F	1.4 V			
t _{rr} typ.	17 ns			
T _J max.	150 °C			
Diode variation	Single die			

FEATURES

- · Ultrafast recovery time
- Ultrasoft recovery
- Very low I_{RRM}
- Very low Q_{rr}
- · Guaranteed avalanche
- Specified at operating temperature
- opcomed at operating temper
- AEC-Q101 qualified
- Meets JESD 201 class 2 whisker test
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912

BENEFITS

- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- · Higher frequency operation
- · Reduced snubbing
- · Reduced parts count

DESCRIPTION / APPLICATIONS

These diodes are optimized to reduce losses and EMI / RFI in high frequency power conditioning systems. The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for freewheeling, flyback, power converters, motor drives, and other applications where high speed and reduced switching losses are design requirements.

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Cathode to anode voltage	V_{RRM}		600	V
Maximum continuous forward current	I _{F(AV)}	T _C = 100 °C	4	
Single pulse forward current	I _{FSM}		25	А
Repetitive peak forward current	I _{FRM}	T _C = 116 °C	16	
Maximum power dissipation	P_{D}	T _C = 100 °C	10	W
Operating junction and storage temperatures	T _J , T _{Stg}		-55 to +150	°C





ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	600	-	-	
Forward voltage V _F	I _F = 4 A	-	1.5	1.8	V	
	I _F = 8 A	-	1.8	2.2		
. s . · · · · ·		I _F = 4 A, T _J = 125 °C	-	1.4	1.7	
Maximum reverse		V _R = V _R rated	=	0.17	3.0	
leakage current	$T_J = 125 ^{\circ}\text{C}, V_R = 0.8 \text{x} V_R \text{rated}$	=	44	300	μA	
Junction capacitance	C _T	V _R = 200 V	=	4	8	pF
Series inductance	L _S	Measured lead to lead 5 mm from package body - 8.0		-	nH	

DYNAMIC RECOVERY CHARACTERISTICS (T _C = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		I _F = 1.0 A, dI _F /dt = 200 A/μA, V _R = 30 V		-	17	-	
Reverse recovery time	t _{rr}	T _J = 25 °C		-	28	42	ns
	T _J = 125 °C		-	38	57		
Peak recovery current	I	T _J = 25 °C	I _F = 4 A dI _F /dt = 200 A/μs V _R = 200 V	-	2.9	5.2	Α
reak recovery current	IRRM	T _J = 125 °C		-	3.7	6.7	
Reverse recovery charge	0	T _J = 25 °C		-	40	60	nC
Reverse recovery charge Q _{rr}	T _J = 125 °C		-	70	105	110	
Rate of fall of recovery current dI _{(rec)M} /dt	dl/d+	T _J = 25 °C		-	280	=	- A/μs
	ui(rec)M/ut	T _J = 125 °C		-	235	_	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	150	°C
Thermal resistance, junction to case	R _{thJC}		-	-	5.0	°C/W
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80	C/VV
Weight			-	2.0	-	g
vveignt			-	0.07	-	oz.
Mounting torque		6.0	_	12	kgf · cm	
Wounting torque			(5.0)	_	(10)	(lbf · in)
Marking device		Case style TO-252AA (D-PAK)	HFA04SD60SH			

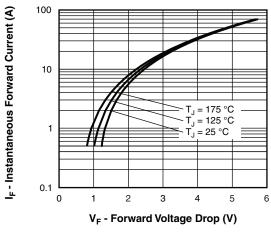


Fig. 1 - Typical Forward Voltage Drop Characteristics

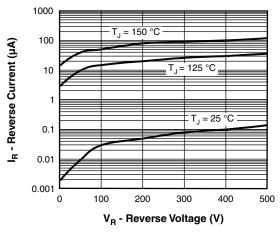


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

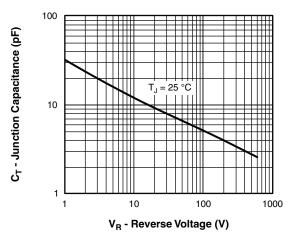


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

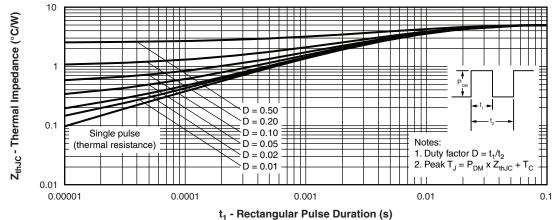


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics



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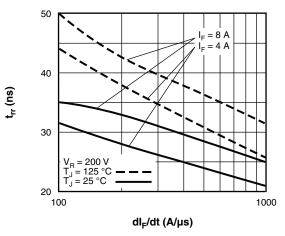


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt

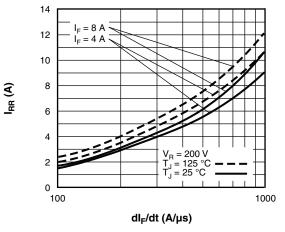


Fig. 6 - Typical Recovery Current vs. dl_F/dt

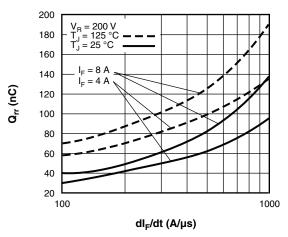


Fig. 7 - Typical Stored Charge vs. dl_F/dt

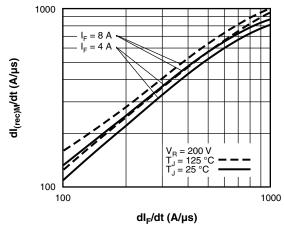


Fig. 8 - Typical dl_{(rec)M}/dt vs. dl_F/dt

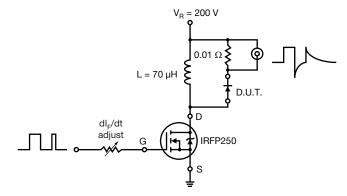
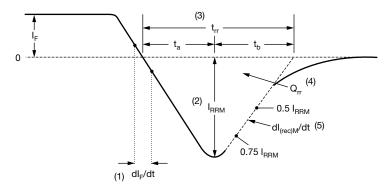


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dI_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

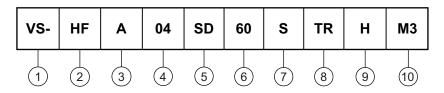
(5) dI_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions



ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

- HEXFRED® family

Electron irradiated

Current rating (04 = 4 A)

5 - D-PAK

Voltage rating (60 = 600 V)

7 - S = D-PAK

8 - • TR = tape and reel

• R = tape and reel (right oriented)

• L = tape and reel (left oriented)

9 - H = AEC-Q101 qualified

10 - Environmental digit:

M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)					
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION		
VS-HFA04SD60SHM3	75	3000	Antistatic plastic tube		
VS-HFA04SD60STRHM3	2000	2000	13" diameter reel		
VS-HFA04SD60STRRHM3	3000	3000	13" diameter reel		
VS-HFA04SD60STRLHM3	3000	3000	13" diameter reel		

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95519			
Part marking information	www.vishay.com/doc?95518			
Packaging information	www.vishay.com/doc?95033			



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